

Fig. 3-1: MIS capacitor fabrication process flow

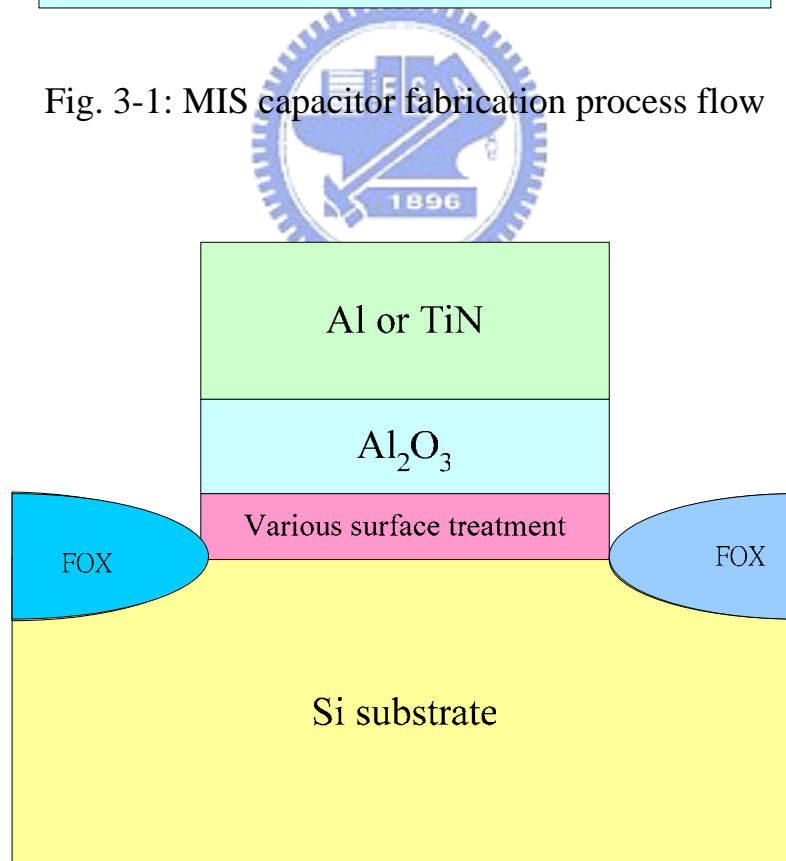


Fig. 3-2: MIS capacitor structure

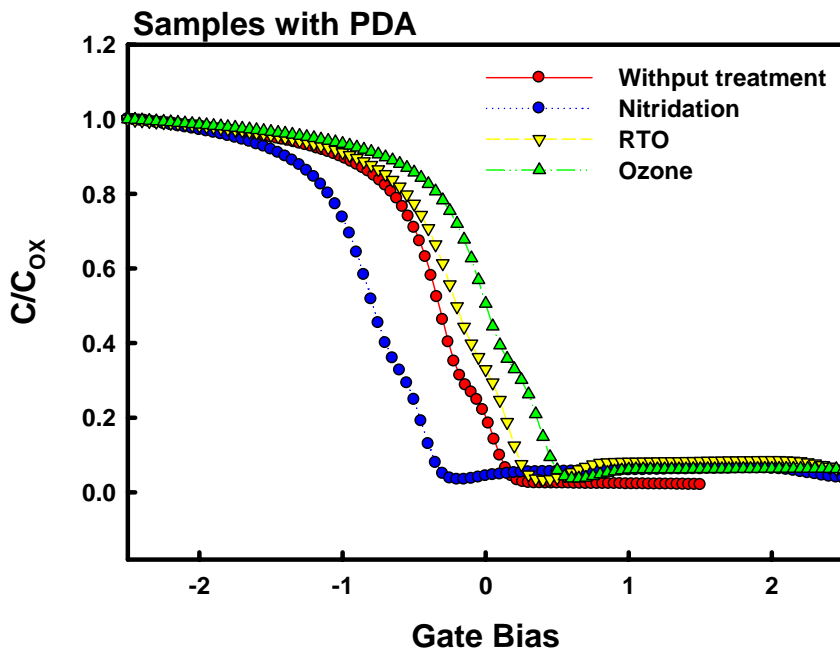
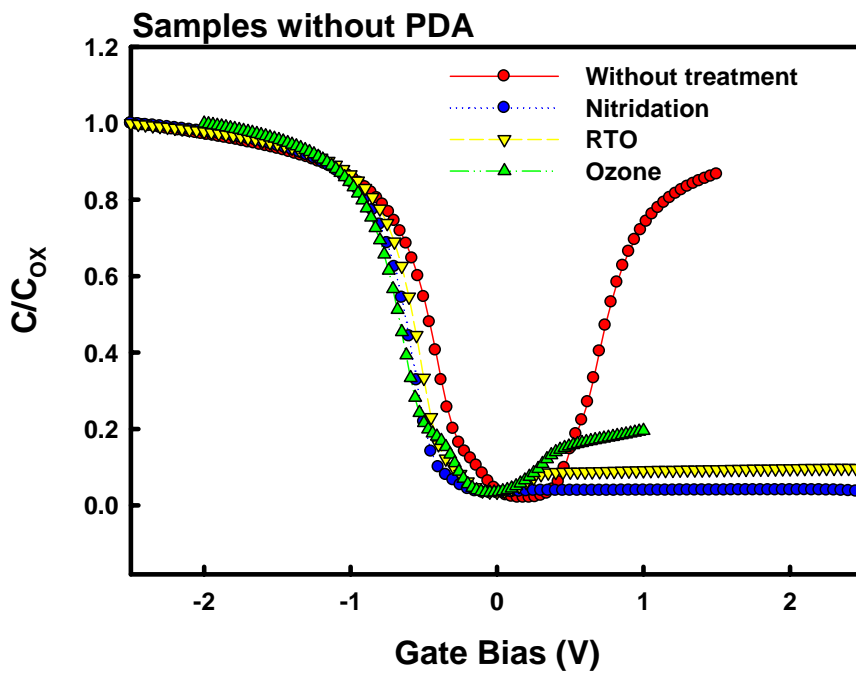


Fig. 3-3: CV curves for samples w/o and with PDA

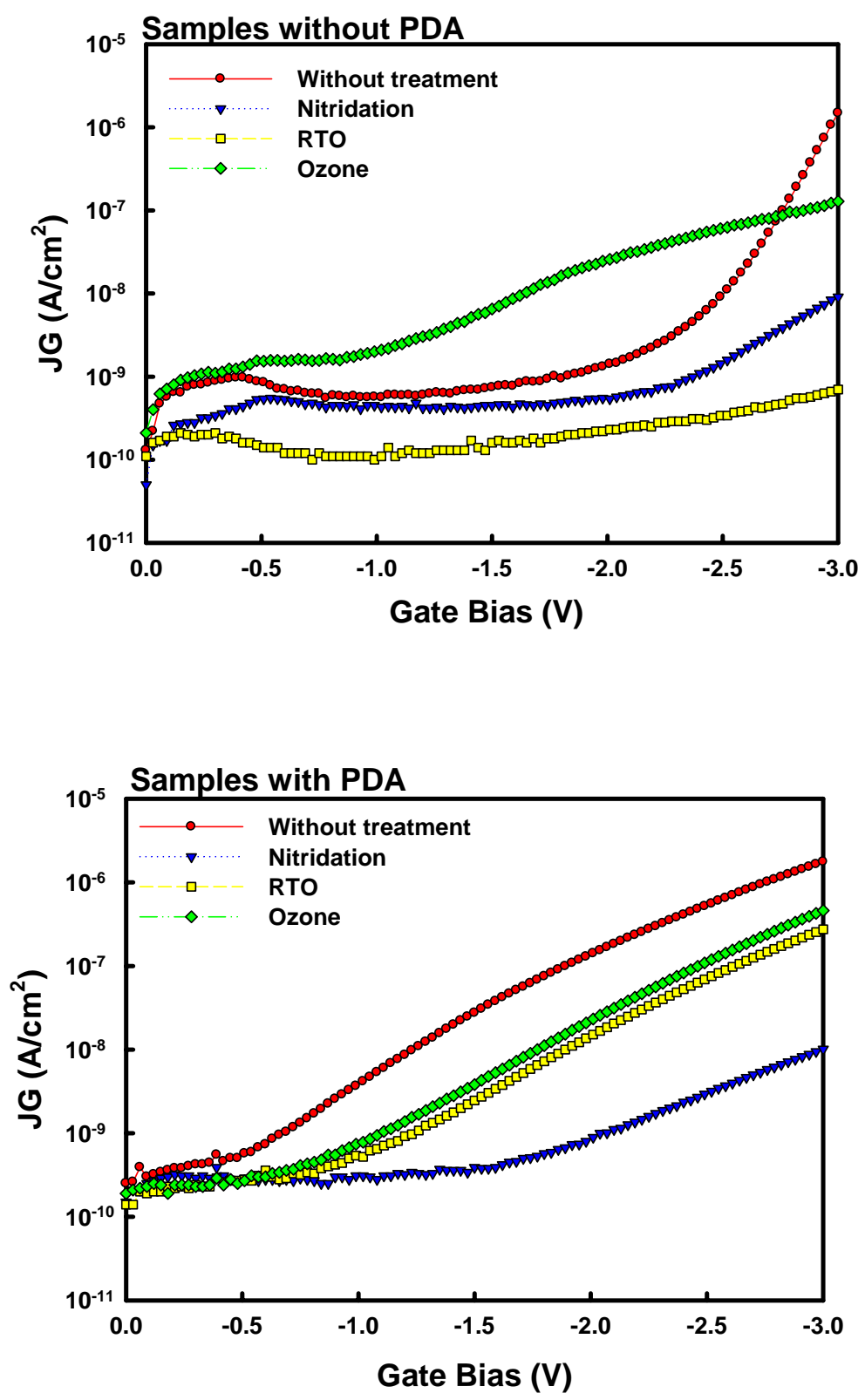


Fig. 3-4: Leakage current density versus gate bias curves for samples with and without PDA process at 900°C

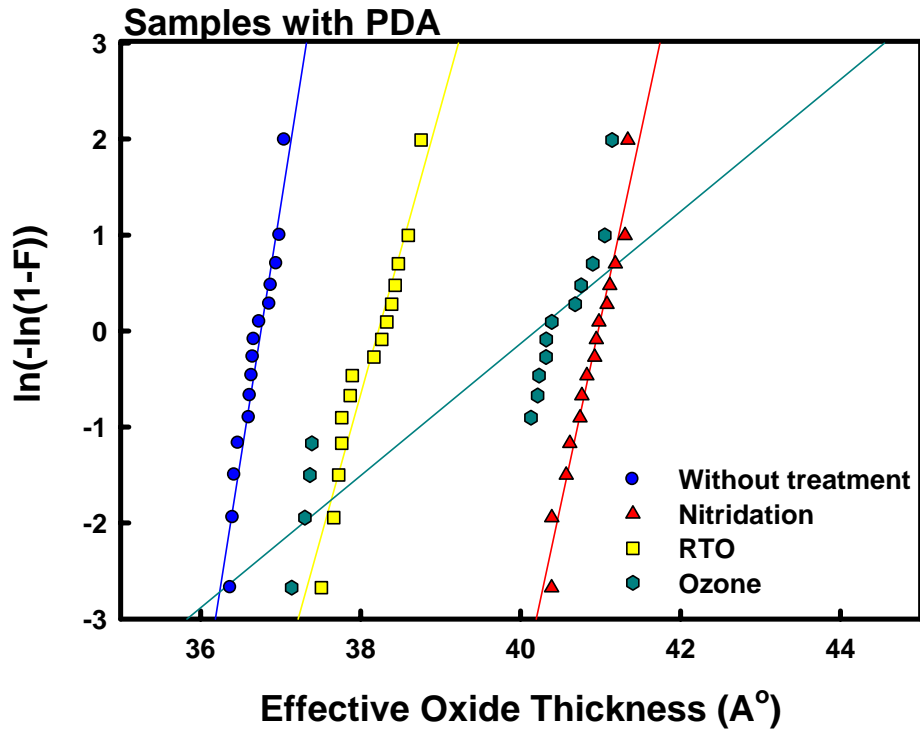
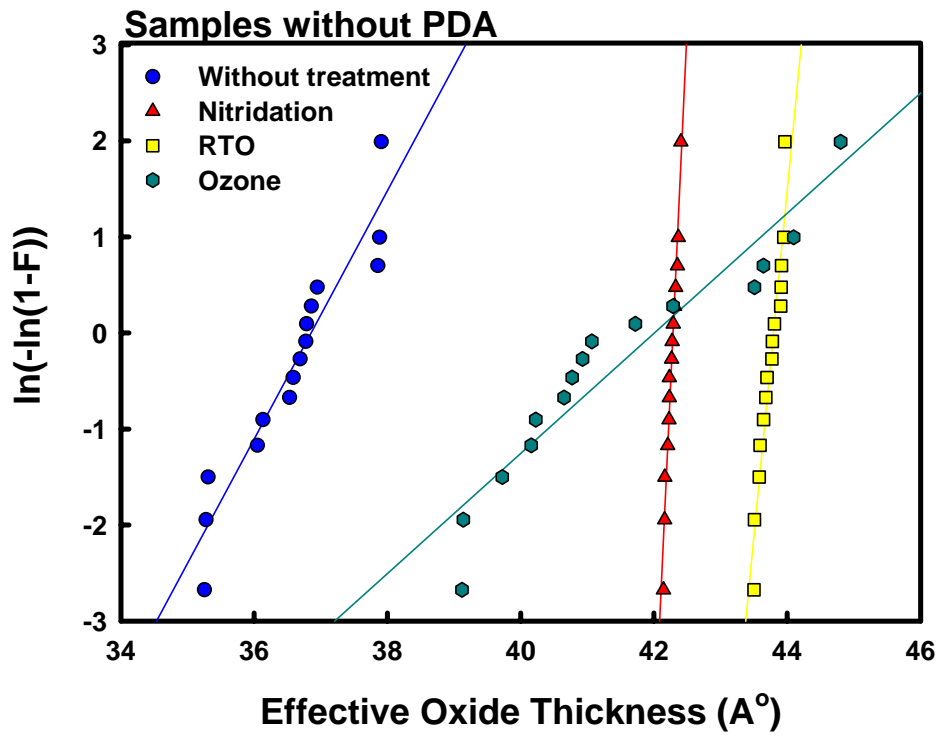


Fig. 3-5: Weibull plots for effective oxide thickness

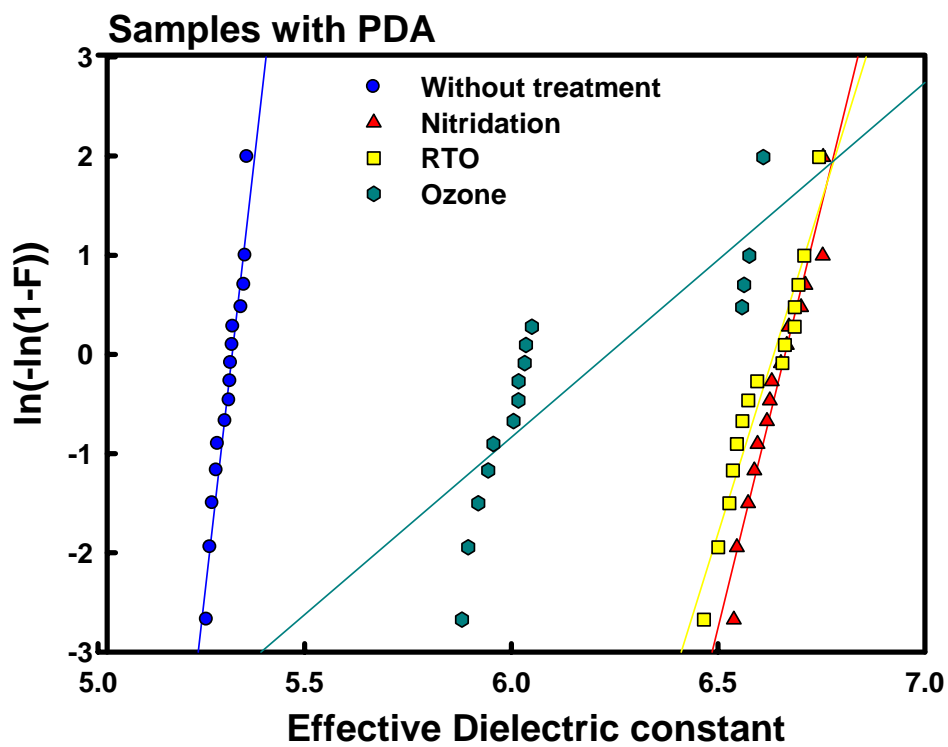
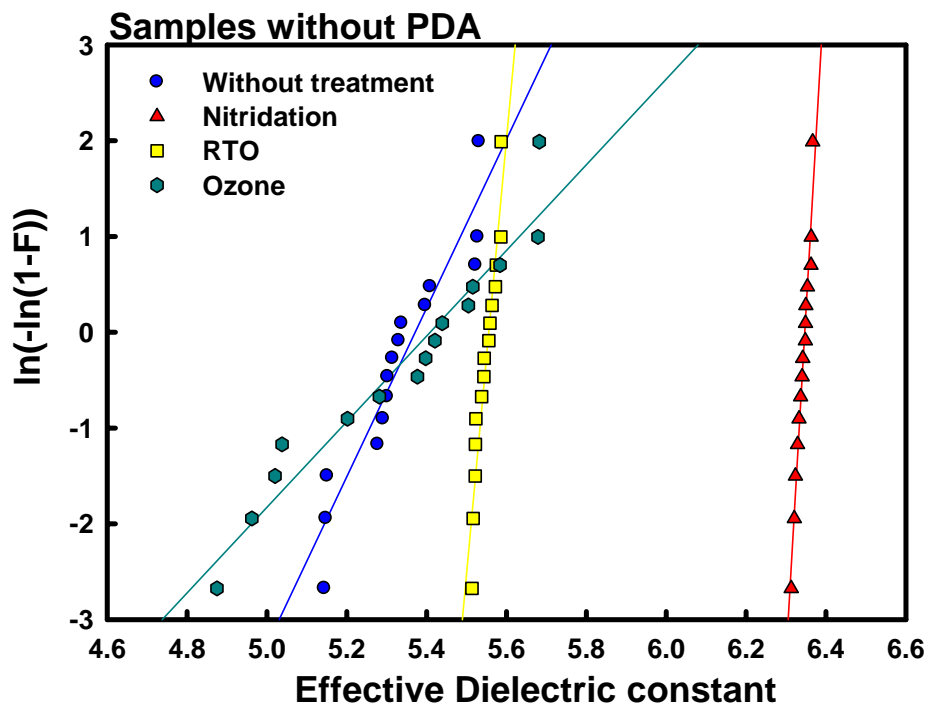


Fig 3-6: Weibull plots for effective dielectric constant

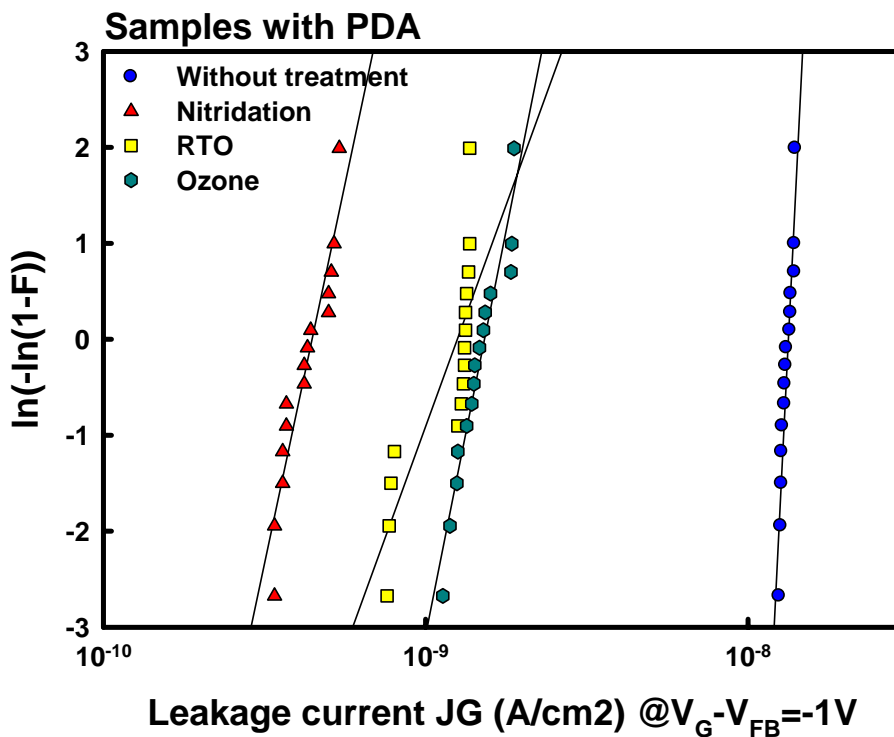
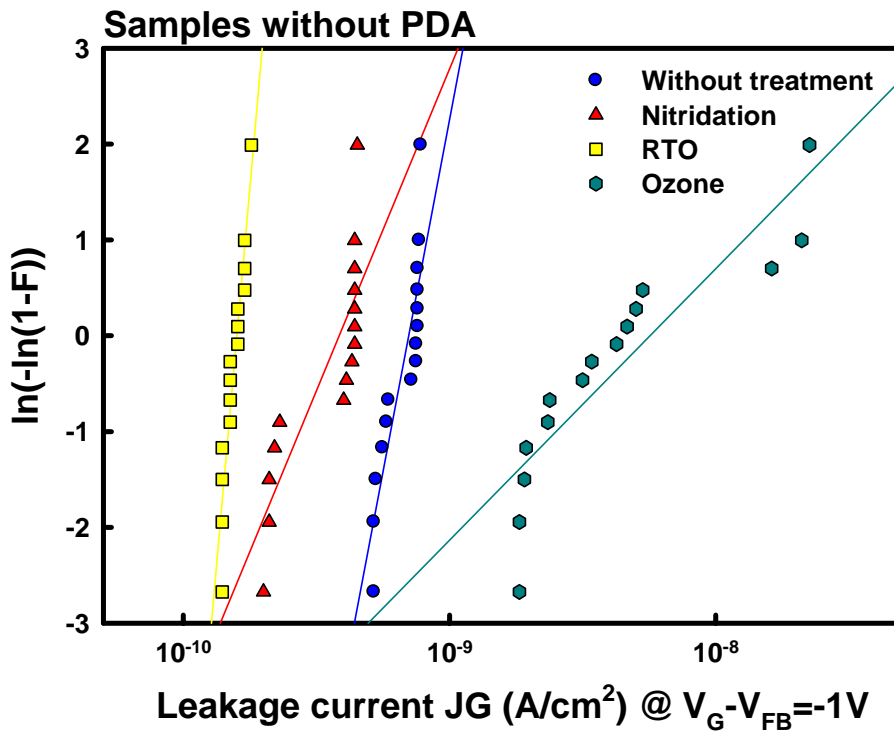


Fig. 3-7: Weibull plots for leakage current at $V_G - V_{FB} = -1V$

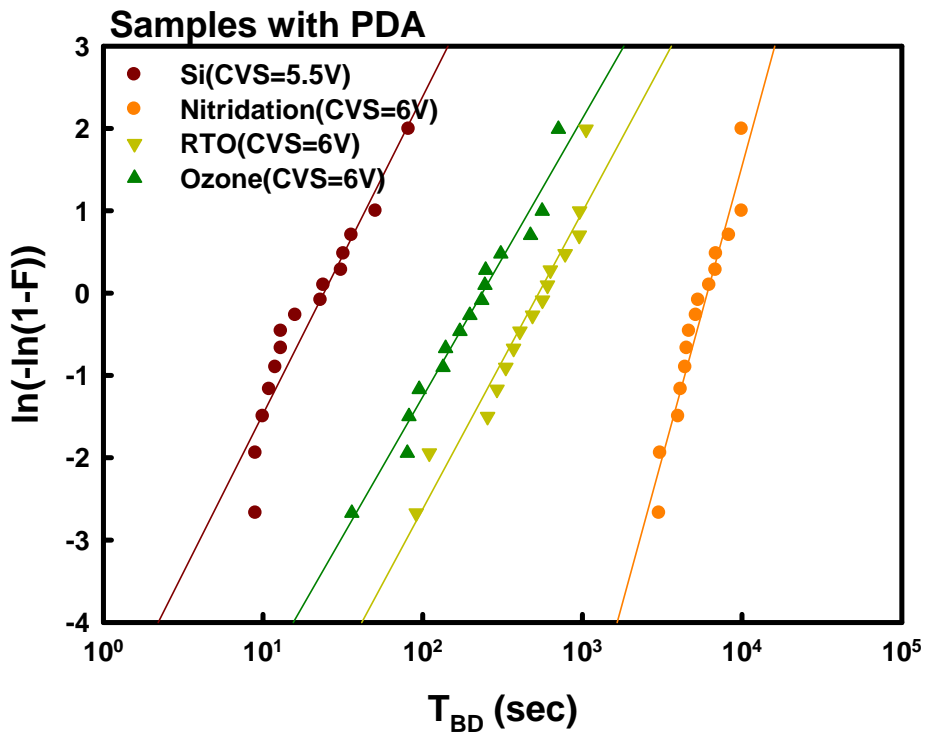
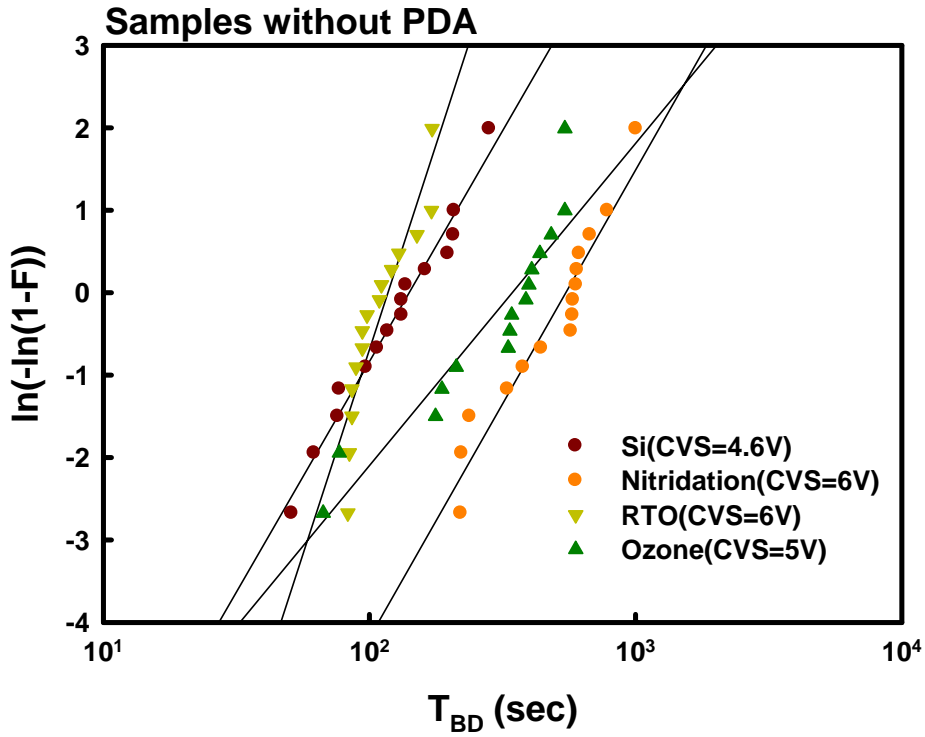


Fig. 3-8 Weibull plots for time depend dielectric breakdown

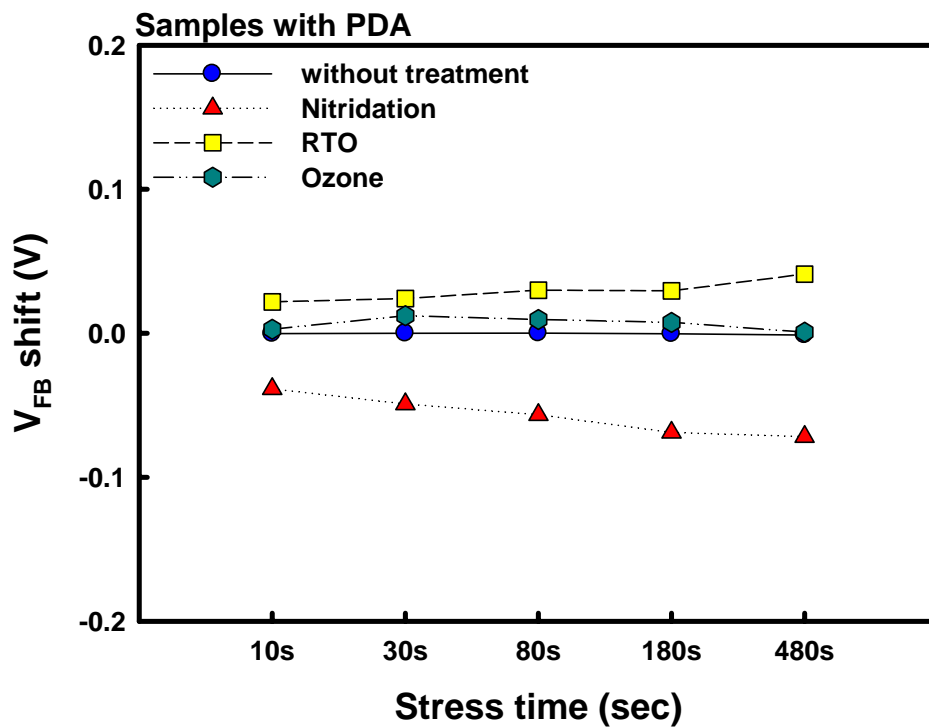
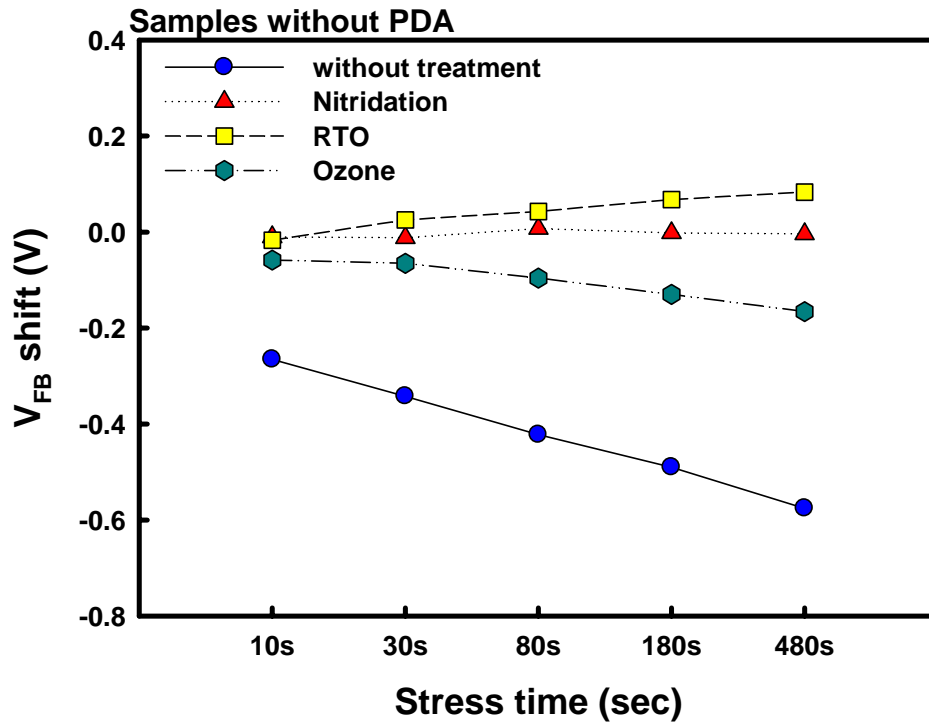


Fig. 3-9: Constant voltage stress ($V_G = -3.5V$) induced flatband voltage shift

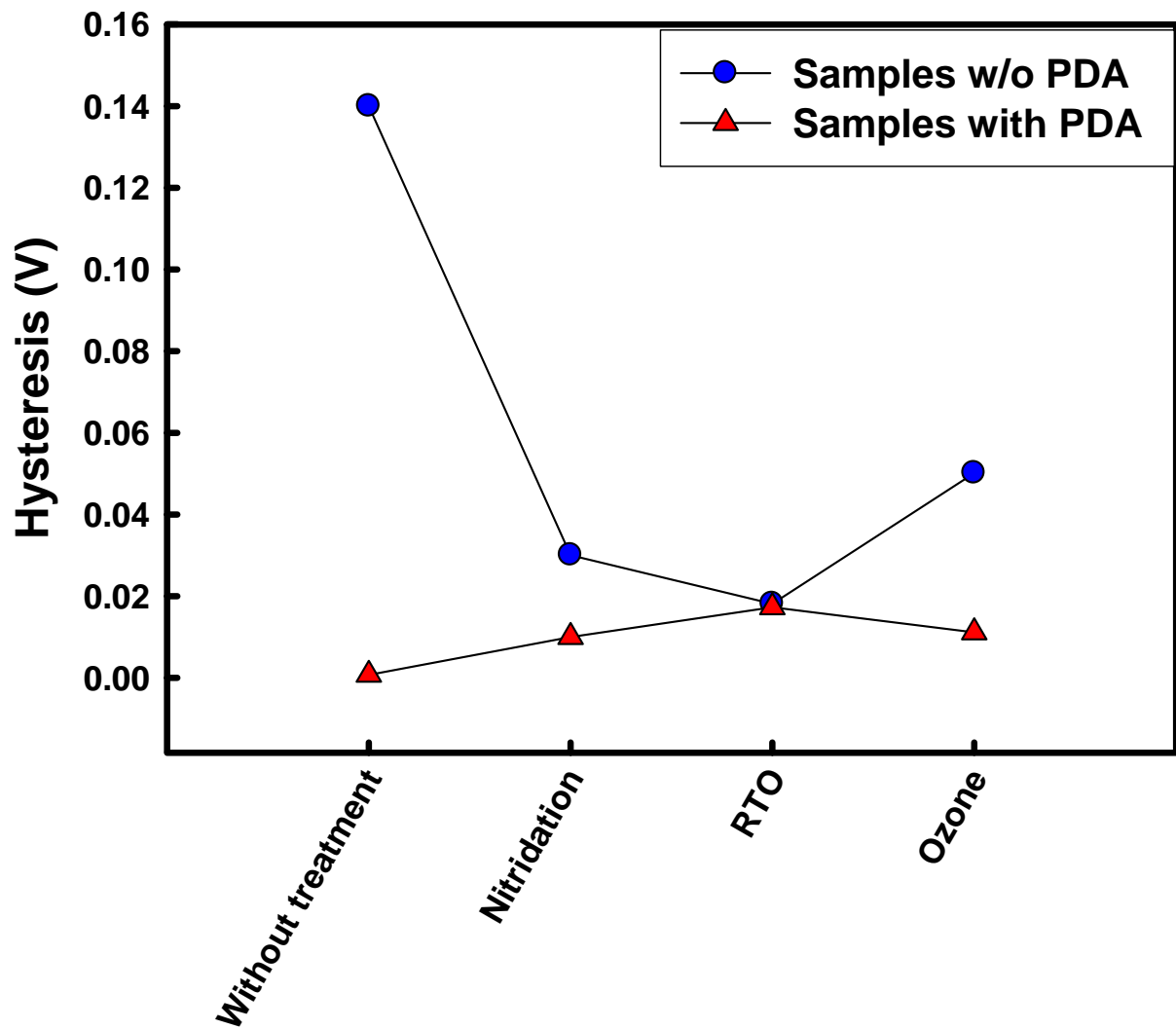


Fig. 3-10: hysteresis curve for samples with and w/o treatment

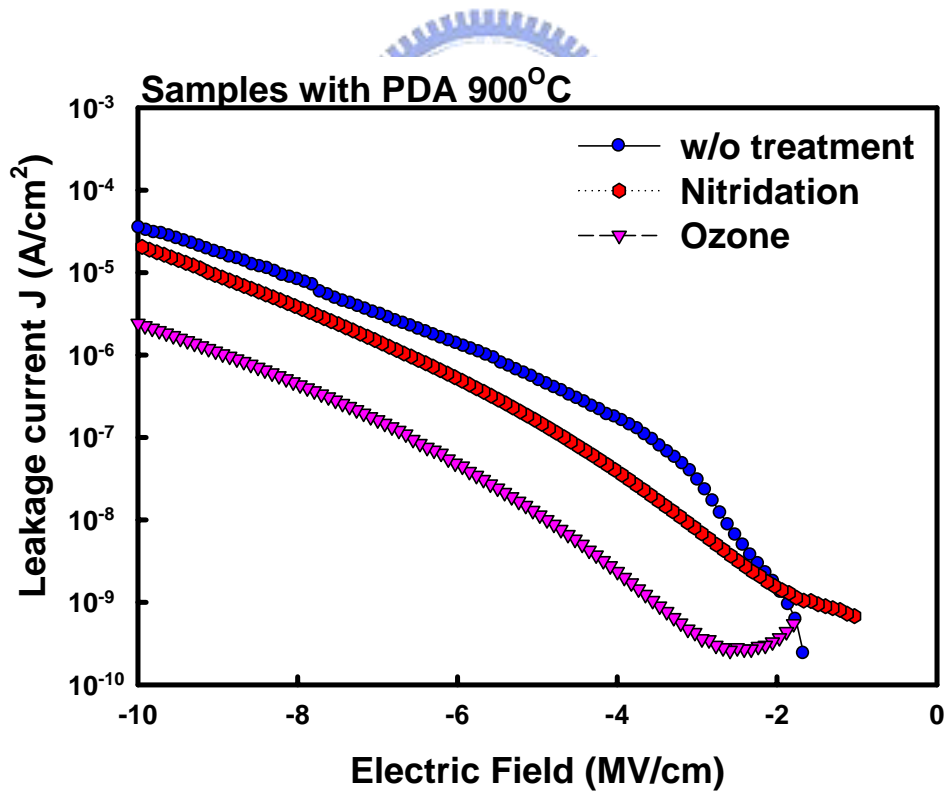
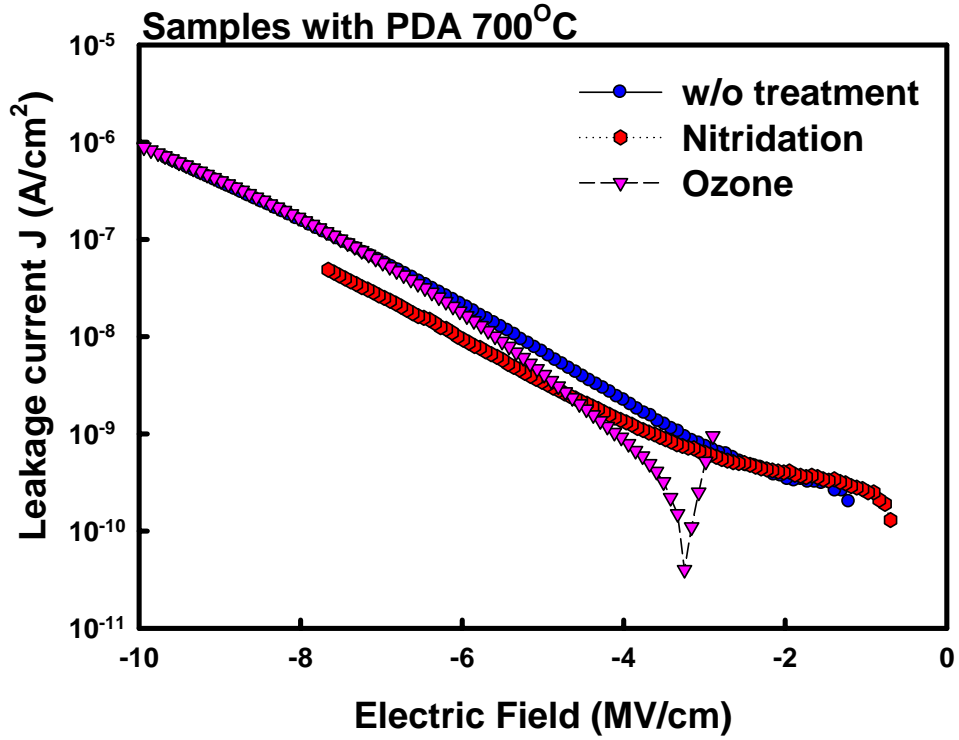


Fig. 3-11: Leakage current density versus electric field for samples with PDA 700°C and PDA 900°C

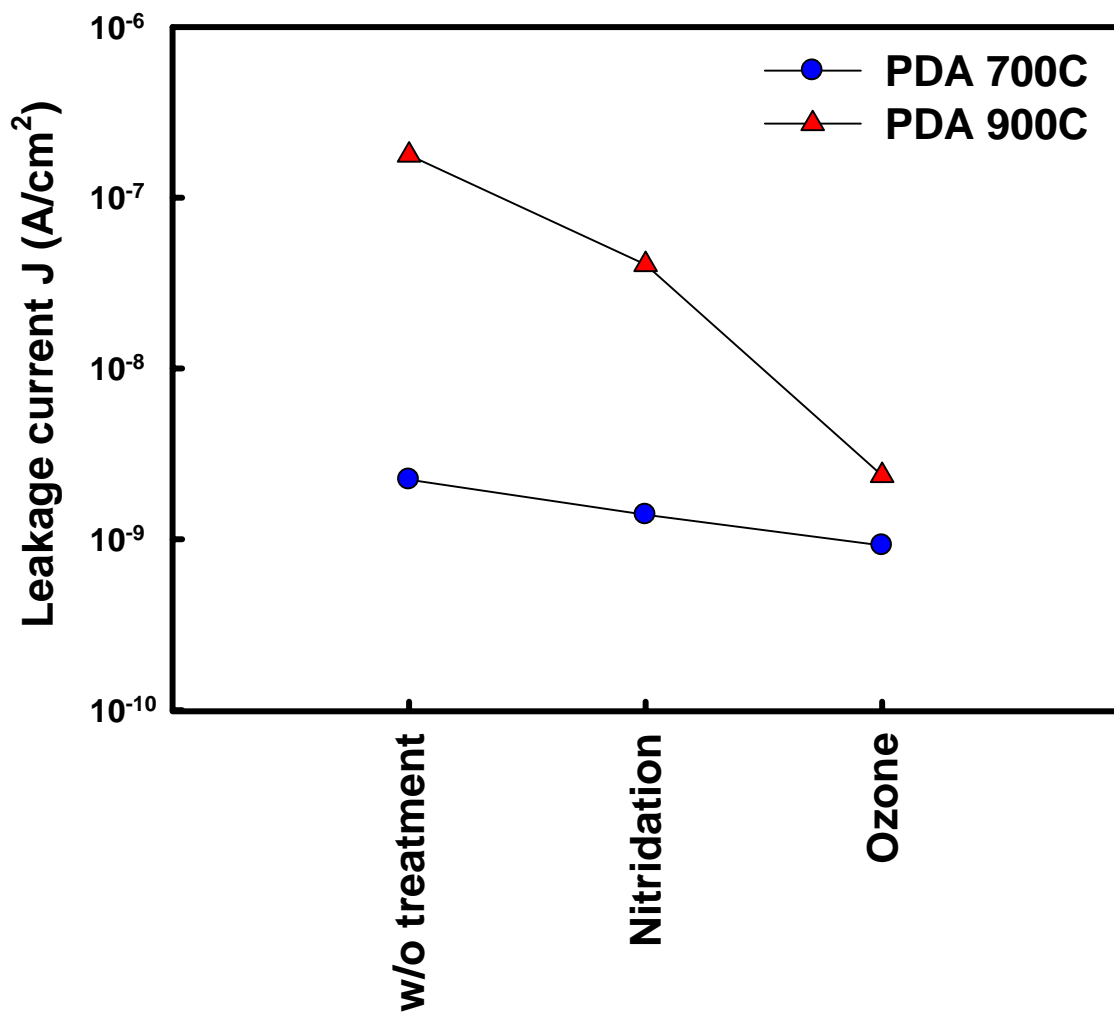


Fig. 3-12: Leakage current density comparison at 4MV/cm

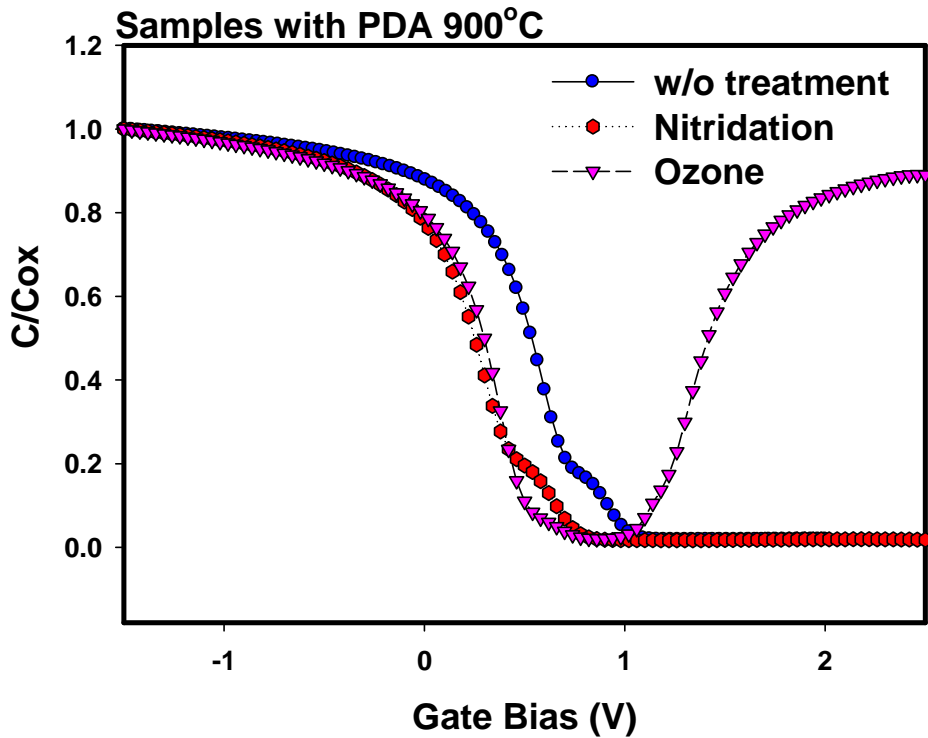
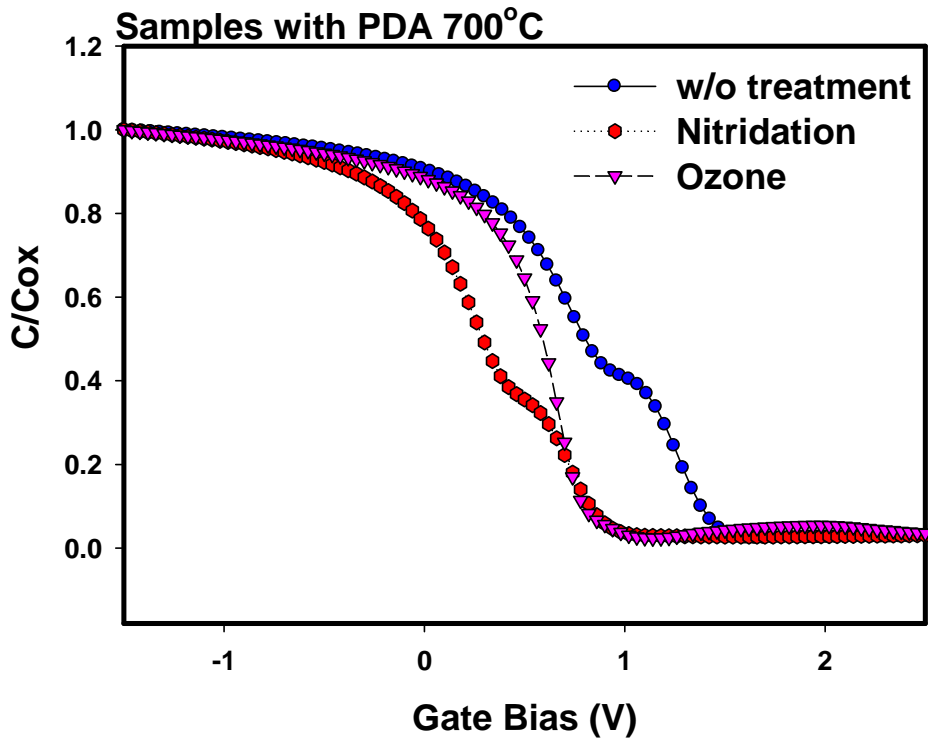
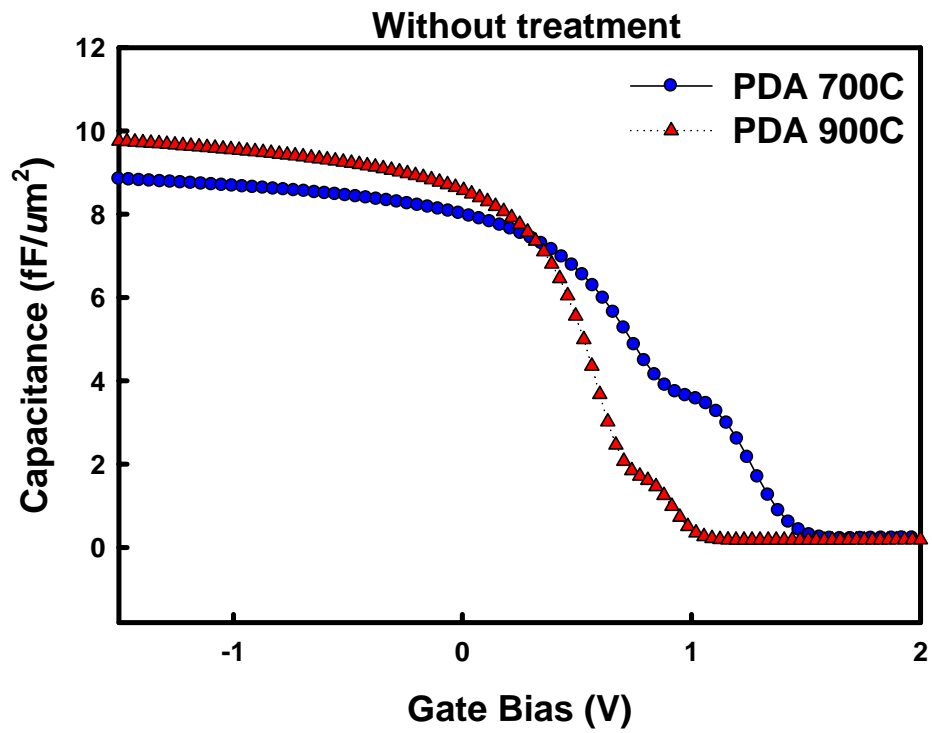
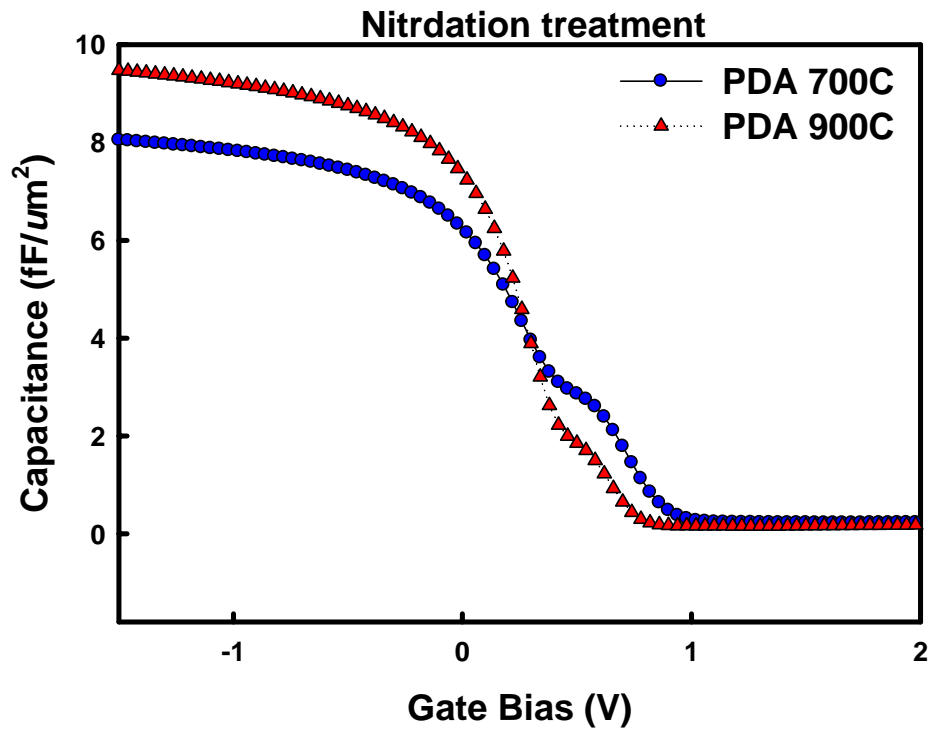


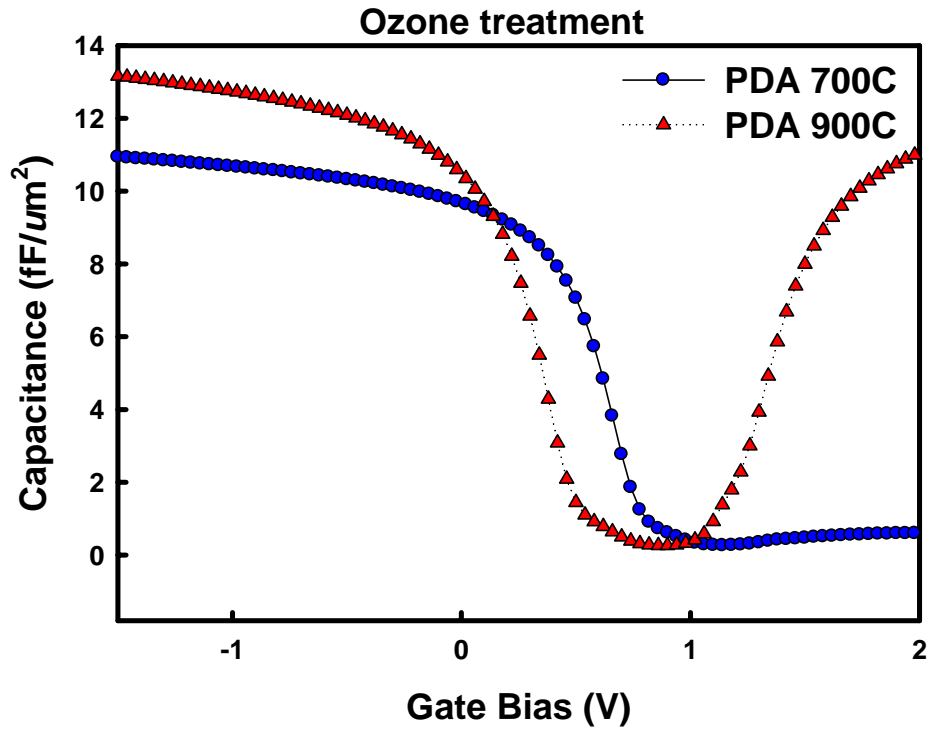
Fig. 3-13: C/C_{ox} versus gate bias for samples with PDA 700°C and PDA 900°C



(a)



(b)



(c)

Fig. 3-14(a)(b)(c): The C-V curve for various surface treatments

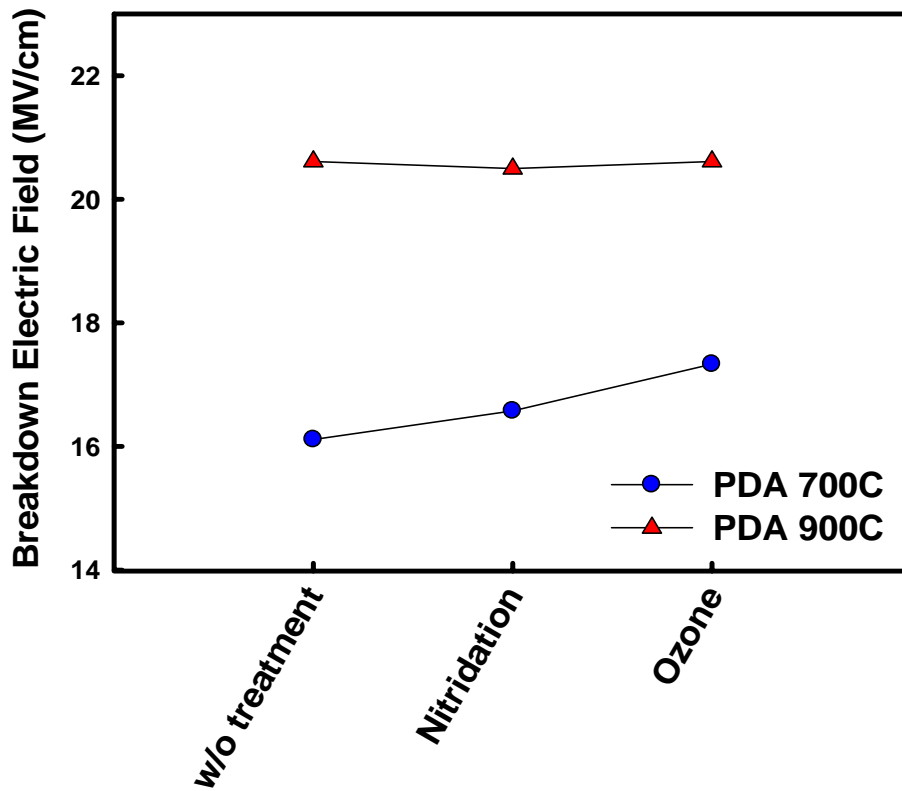


Fig. 3-15: Breakdown characteristic for all samples

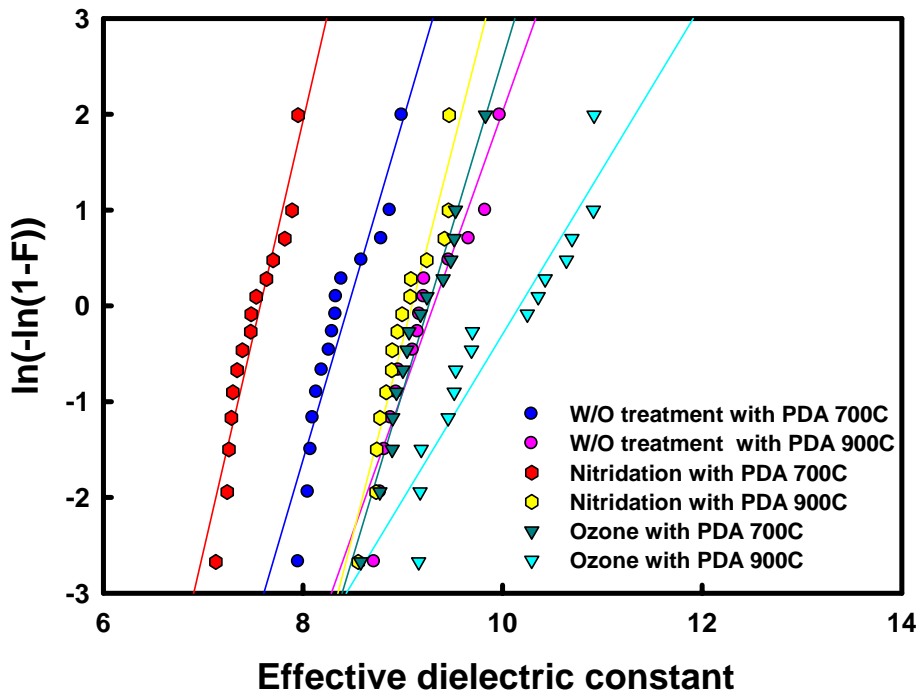


Fig. 3-16: Weibull plots of Effective k value for various surface treatments

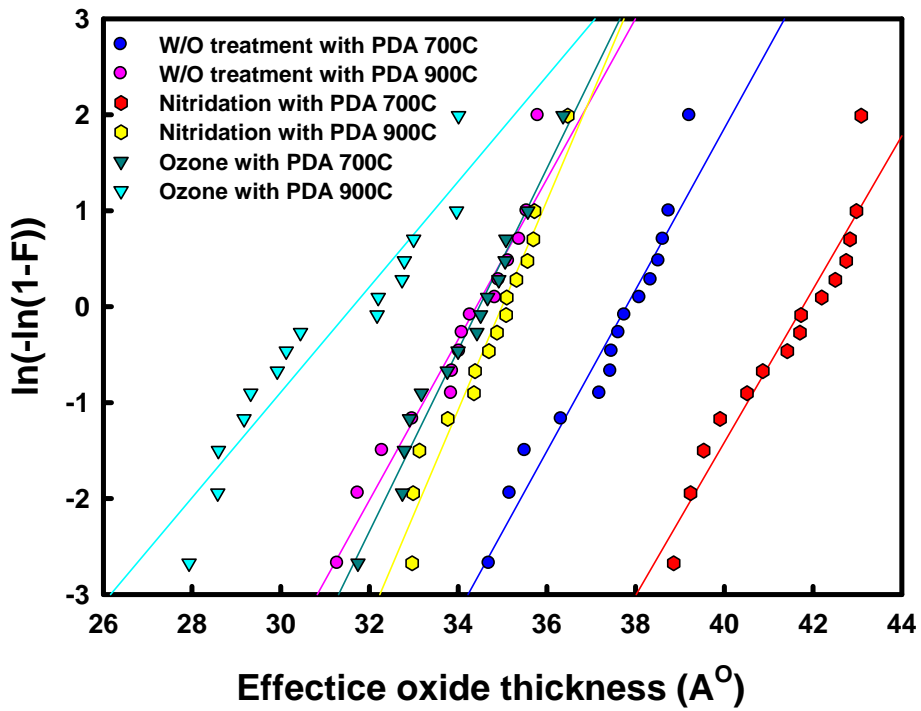


Fig. 3-17: Weibull plots of Effective oxide thickness

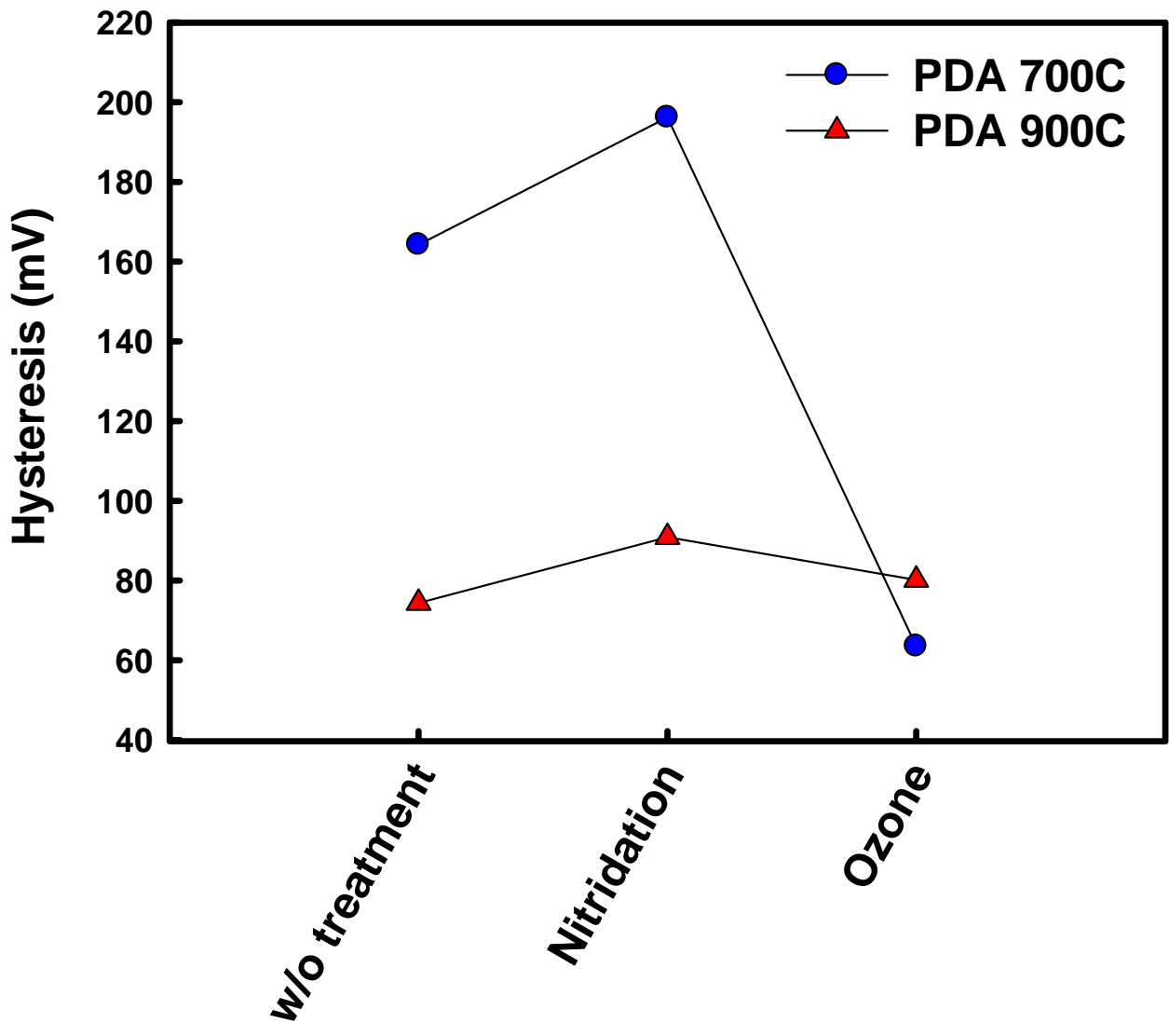


Fig. 3-18: Hysteresis characteristic for all samples

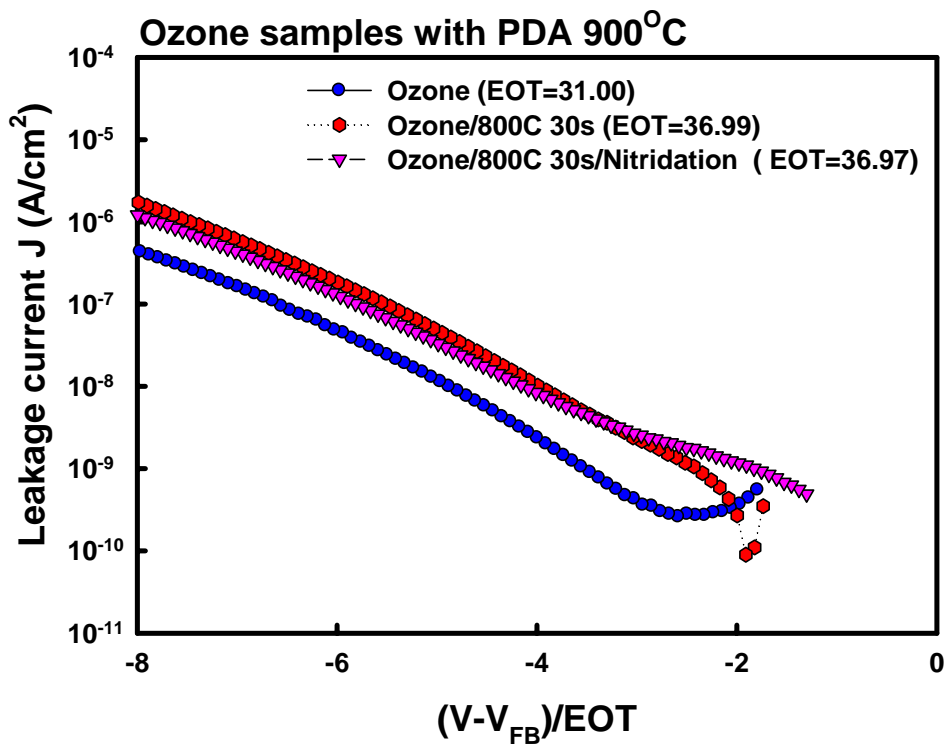
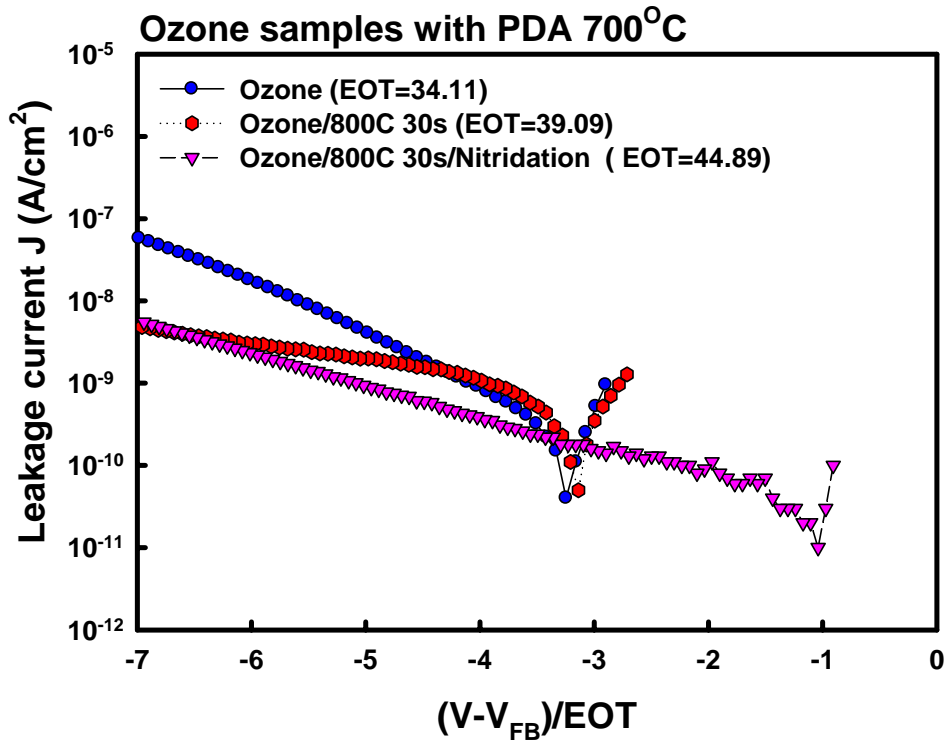


Fig. 3-19: Leakage current density versus electric field for various ozone treatments

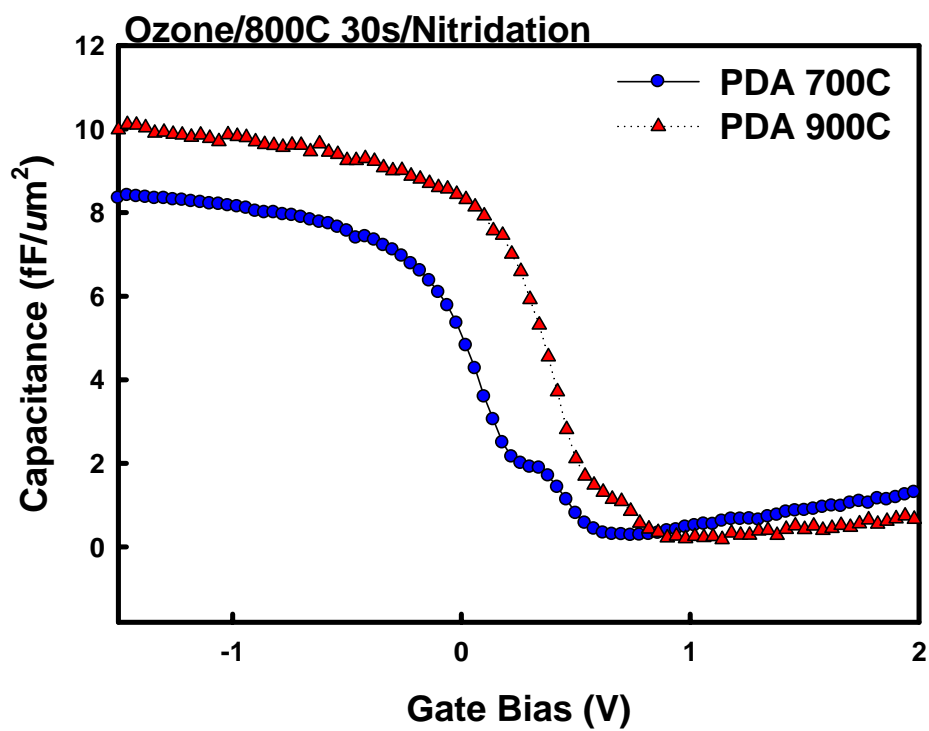
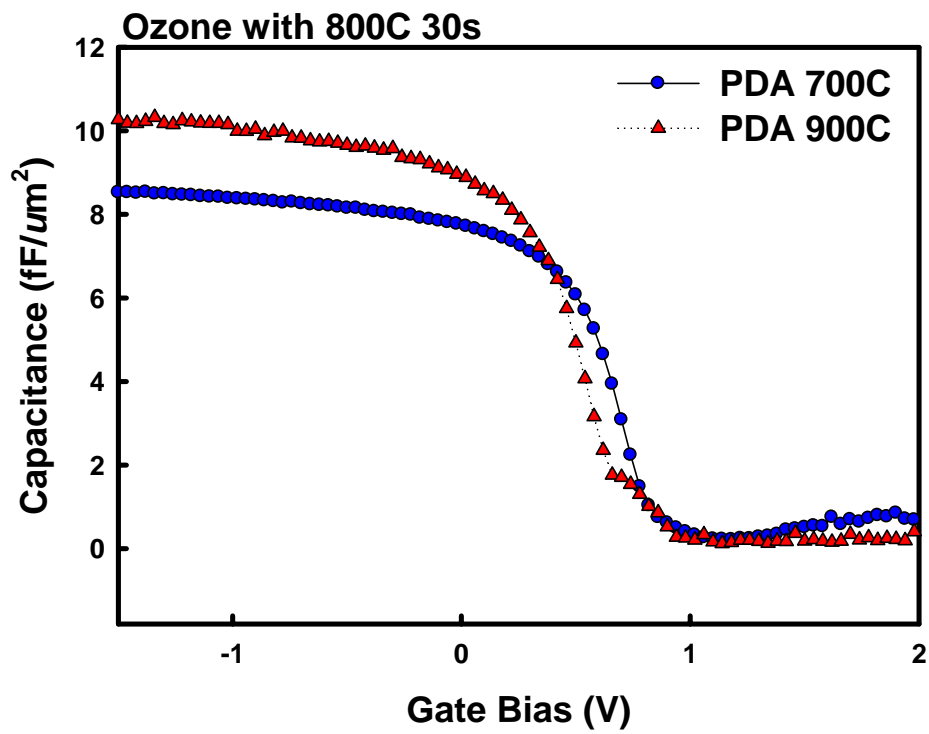


Fig. 3-20: The C-V curve for various ozone treatments

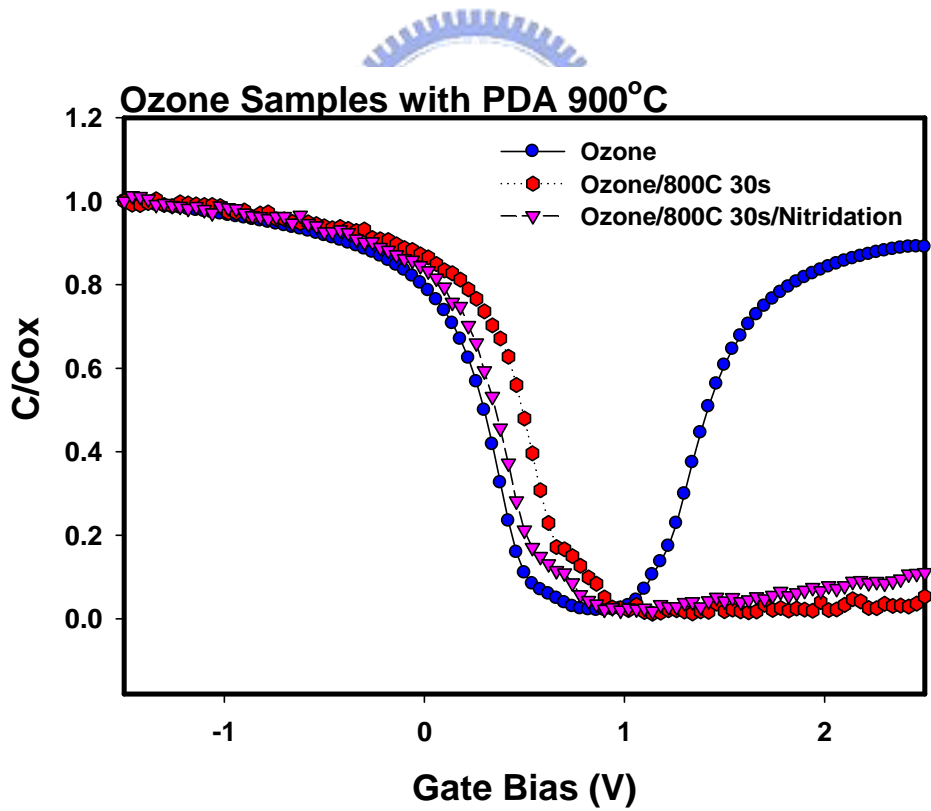
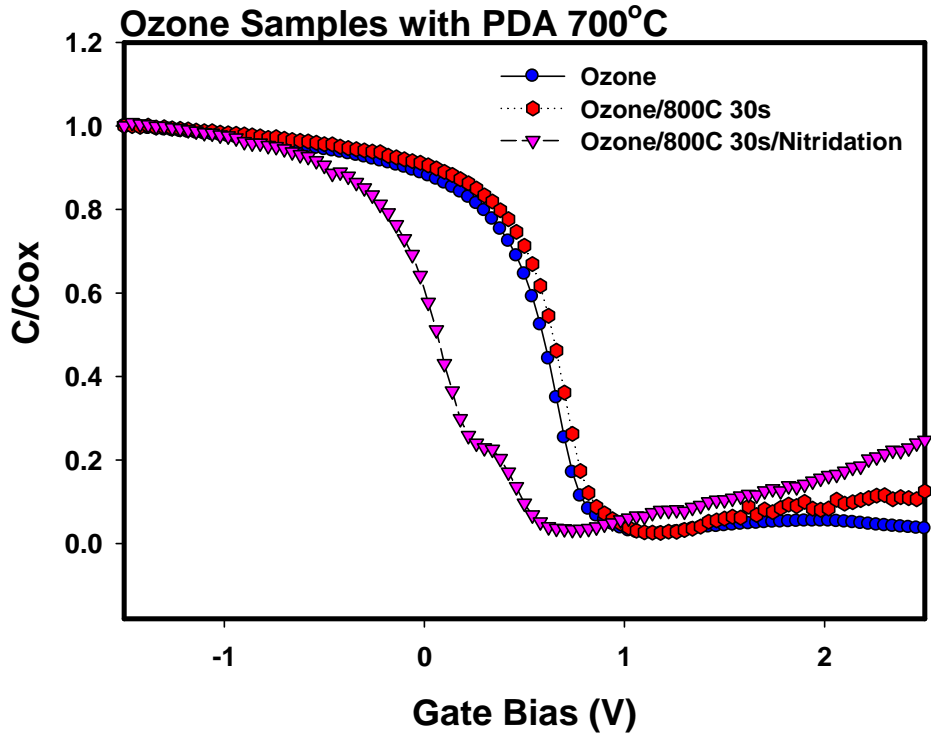


Fig. 3-21: The C/C_{ox} curve for various ozone treatments with PDA 700°C and PDA 900°C

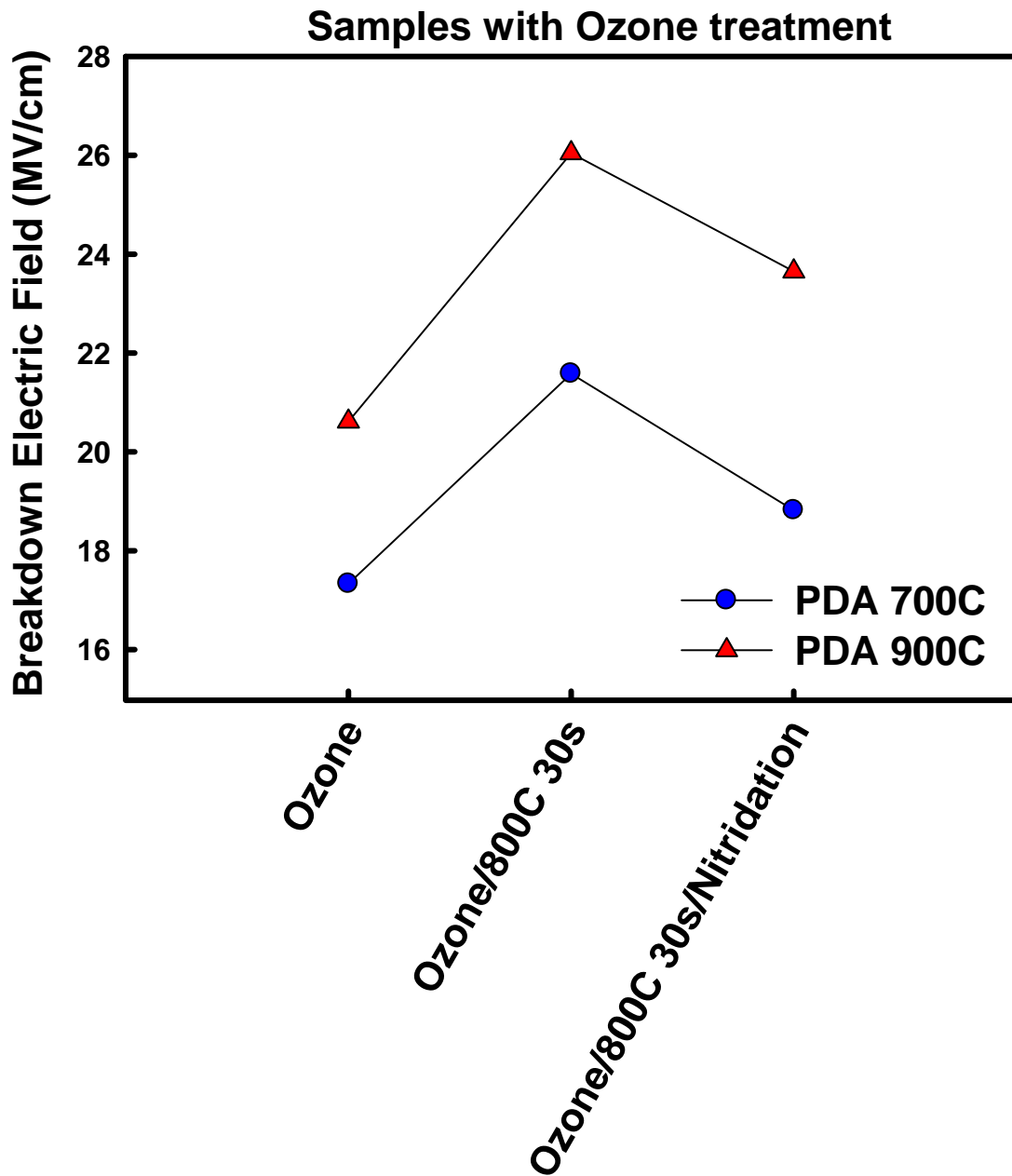


Fig. 3-22: Breakdown characteristic for various ozone treatments with PDA 700°C and PDA 900°C

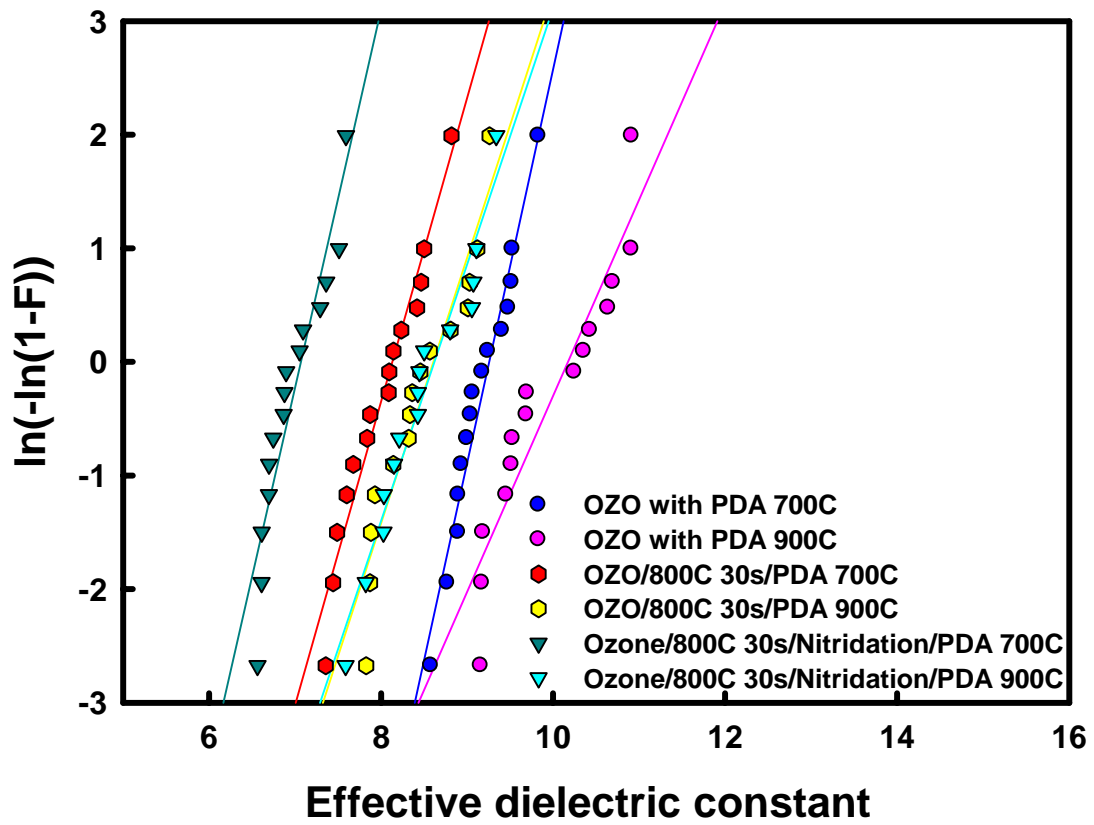


Fig. 3-23: Effective dielectric constant for various ozone treatments with PDA 700°C and PDA 900°C